

**Shantou Huashan Electronic Devices Co.,Ltd.**

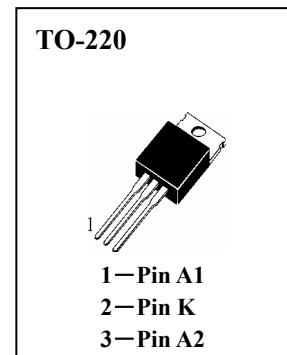
**HJP2060CT**

## 20A SCHOTTKY BARREIER RECTIFIER

### ■ Features

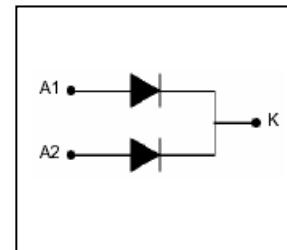
- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheelings, and Polarity Protection Applications

### ■ Package



### ■ Maximum Ratings

- $T_{stg}$  — Storage Temperature ..... -65~150°C
- $T_j$  — Operating Temperature ..... -65~150°C
- $V_{RRM}$  — Peak Repetitive Reverse Voltage ..... 60V
- $V_{RWM}$  — Working Peak Reverse Voltage ..... 60V
- $V_R$  — DC Blocking Voltage ..... 60V
- $V_{R(RMS)}$  — RMS Reverse Voltage ..... 42V
- $I_{F(AV)}$  — Average Rectified Output Current@ $T_c=95^\circ\text{C}$  ..... Double Dies 20A
  - ◆ (Note 1) ..... Single Die 10A
- $I_{FSM}$  — Non-Repetitive Peak Forward Surge Current (Single Die, 60Hz) ..... 200A



### ■ Electrical Characteristic@ $T_a=25^\circ\text{C}$ unless otherwise specified

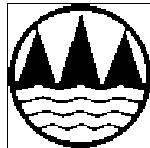
Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Characteristic	Symbol	Min	Max	Unit	Condition
Forward Voltage Drop	$V_{FM}$		0.75	V	$I_F=10\text{A}, T_C=25^\circ\text{C}$
Peak Reverse Current at Rated DC Blocking Voltage	$I_{RM}$		1.0 50	mA	$V_R = V_{RRM} \quad T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Typical Junction Capacitance(Note 2)	$C_J$		1100	pF	
Typical Thermal Resistance Junction to Case(Note 1)	$R_{th-j}$		2.8	°C/W	

Notes: 1、 Thermal resistance junction to case mounted on heatsink.

2、 Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V DC.



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## ■ PERFORMANCE CURVES

